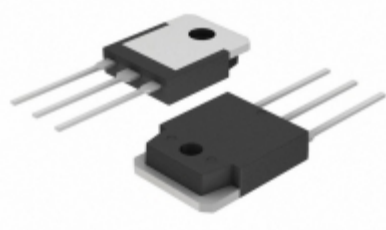


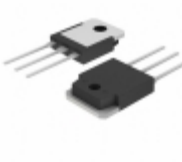



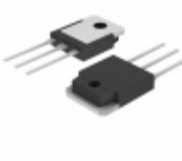
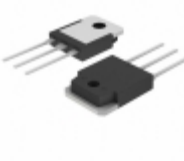

	GP2M012A080NG	
	Hersteller-Teilenummer:	GP2M012A080NG
	Hersteller / Marke:	Global Power Technologies Group
	Teil der Beschreibung:	MOSFET N-CH 800V 12A TO3PN
	Datenblätter:	 GP2M012A080NG.pdf
	RoHs Status:	Bleifrei / RoHS-konform
<p>Image may be representation. See specs for product details.</p>	Lagerzustand:	New original, 1700 pcs Stock Available.
	Liefern von:	Hong Kong
	Versandweg:	DHL/Fedex/TNT/UPS/EMS

Spezifikationen

Teilenummer	GP2M012A080NG
Hersteller	Global Power Technologies Group
Beschreibung	MOSFET N-CH 800V 12A TO3PN
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	1700 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-3P-3, SC-65-3
Supplier Device-Gehäuse	TO-3PN
Verlustleistung (max)	416W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	800V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	12A (Tc)
Rds On (Max) @ Id, Vgs	650 mOhm @ 6A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	79nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	3370pF @ 25V
Verpackung	Tube






















GP2M012A080NG ist neu im Original. Suche GP2M012A080NG Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie GP2M012A080NG Global Power Technologies Group mit Garantie und Vertrauen. Anfrage GP2M012A080NG: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>GP2M012A060F Global Power Technologies Group MOSFET N-CH 600V 12A TO220F</p>	 <p>GP2M020A050N Global Power Technologies Group MOSFET N-CH 500V 20A TO3PN</p>	 <p>GP2M020A050H Global Power Technologies Group MOSFET N-CH 500V 18A TO220</p>	 <p>GP2M020A050F Global Power Technologies Group MOSFET N-CH 500V 18A TO220F</p>
 <p>GP2M012A060H Global Power Technologies Group MOSFET N-CH 600V 12A TO220</p>	 <p>GP2M011A090NG Global Power Technologies Group MOSFET N-CH 900V 11A TO3PN</p>	 <p>GP2M020A060N Global Power Technologies Group MOSFET N-CH 600V 20A TO3PN</p>	 <p>GP2M010A065H Global Power Technologies Group MOSFET N-CH 650V 9.5A TO220</p>

heiße Teile

Mehr

 GP2A25J0000F	 GP2A25NJ	 GP2A28A1J00F	 GP2A28N1J00F	 GP2AP002A00F
 GP2AP002S00F	 GP2AP003A10F	 GP2AP007A00F	 GP2AP008T00F	 GP2AP030A00F
 GP2AP052A00F	 GP2AP052A00F	 GP2L26K2	 GP2M002A060FG	 GP2M004A060PG
 GP2M004A065FG	 GP2M004A065PG	 GP2M005A050PG	 GP2M005A060CG	 GP2M005A060FG
 GP2M005A060PGH	 GP2M008A060FGH	 GP2M010A060F	 GP2M010A065F	 GP2M011A090NG
 GP2M020A050H	 GP2M020A060N	 GP2S24J0000F	 GP2S27T3	 GP2S27T3J00F
 GP2S27V6	 GP2S29SVJ00F	 GP2S40JJ000F	 GP2S700HCP	 GP2S700HCP
 GP2W0004YP	 GP2W0110YPS	 GP2W0112YPOF	 GP2W0118YPS	 GP2W0150YP0F
 GP2W3104XP0F	 GP2W3104YP0F	 GP2W3106YP0F	 GP2W3152YP0F	 GP2W3172XP0F
 GP2W3270XP0F	 GP2Y0A02YK0F	 GP2Y0A02YK0F	 GP2Y0A21	 GP2Y0A21YK0F

Contact us: Info@Y-IC.com

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